# **Complementary Silicon Plastic Power Transistors**

Designed for use in general purpose amplifier and switching applications.

#### **Features**

- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V <sub>CEO</sub>	40 60 80 100	Vdc
Collector-Base Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V <sub>CB</sub>	40 60 80 100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	6.0	Adc
Collector Current – Peak	I <sub>CM</sub>	10	Adc
Base Current	Ι <sub>Β</sub>	2.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	65 0.52	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	62.5	mJ
Operating and Storage Junction, Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	ММ	С	V

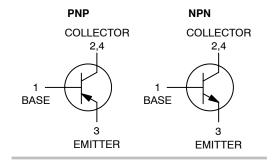
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### ON Semiconductor®

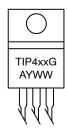
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# 6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS





#### MARKING DIAGRAM



TIP4xx = Device Code xx = 1, 1A, 1B, 1C 2, 2A, 2B, 2C A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

<sup>1.</sup>  $I_C$  = 2.5 A, L = 20 mH, P.R.F. = 10 Hz,  $V_{CC}$  = 10 V,  $R_{BE}$  = 100  $\Omega$ .

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.67	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	57	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	,		•	•
Collector-Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0) TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V <sub>CEO(sus)</sub>	40 60 80 100	- - - -	Vdc
Collector Cutoff Current	I <sub>CEO</sub>	-	0.7 0.7	mAdc
Collector Cutoff Current $ \begin{aligned} &(V_{CE}=40 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41G}, \text{TIP42G} \end{aligned} \\ &(V_{CE}=60 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41AG}, \text{TIP42AG} \end{aligned} \\ &(V_{CE}=80 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41BG}, \text{TIP42BG} \end{aligned} \\ &(V_{CE}=100 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41CG}, \text{TIP42CG} \end{aligned}$	I <sub>CES</sub>	- - -	400 400 400 400	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	1.0	mAdc
ON CHARACTERISTICS (Note 2)	<u> </u>			
DC Current Gain	h <sub>FE</sub>	30 15	- 75	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 6.0 Adc, I <sub>B</sub> = 600 mAdc)	V <sub>CE(sat)</sub>	-	1.5	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 6.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	-	2.0	Vdc
DYNAMIC CHARACTERISTICS	<u>'</u>			•
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	3.0	-	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

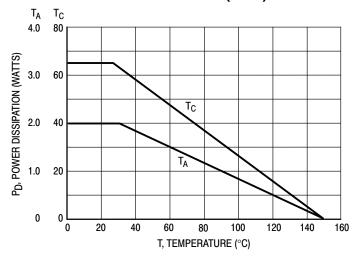
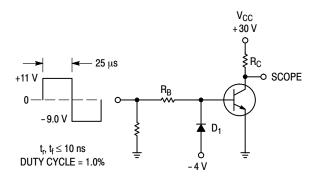


Figure 1. Power Derating



 $\rm R_{\rm B}$  and  $\rm R_{\rm C}$  varied to obtain desired current levels

D $_1$  MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I $_B\approx 100$  mA MSD6100 USED BELOW I $_B\approx 100$  mA

Figure 2. Switching Time Test Circuit

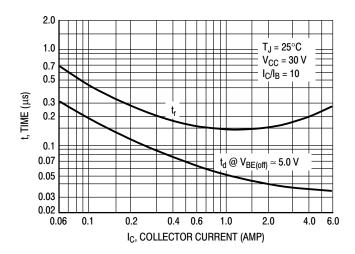


Figure 3. Turn-On Time

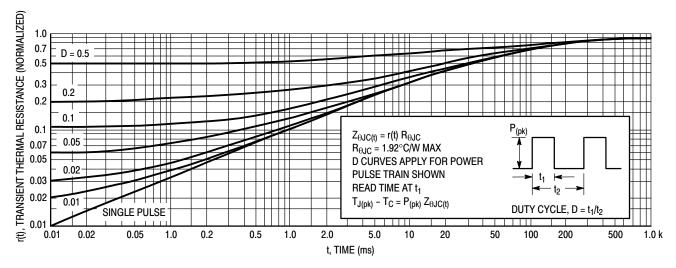


Figure 4. Thermal Response

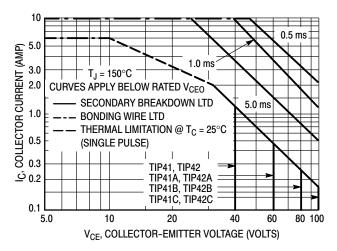


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

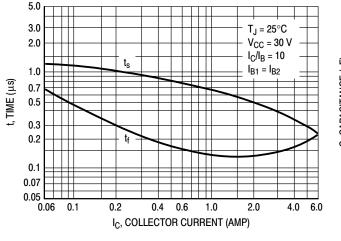


Figure 6. Turn-Off Time

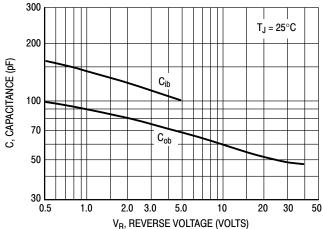


Figure 7. Capacitance

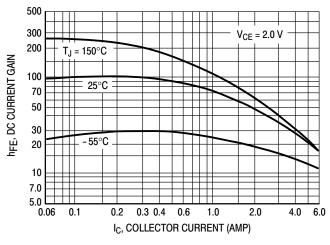


Figure 8. DC Current Gain

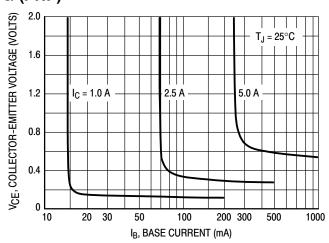


Figure 9. Collector Saturation Region

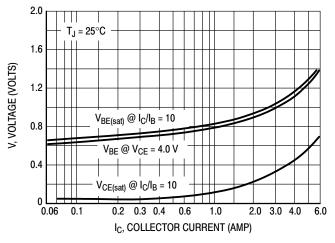


Figure 10. "On" Voltages

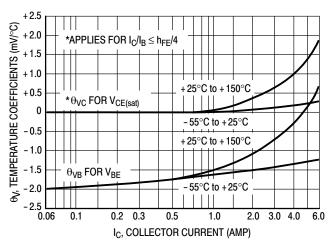


Figure 11. Temperature Coefficients

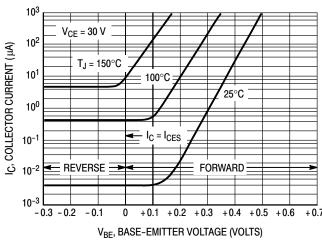


Figure 12. Collector Cut-Off Region

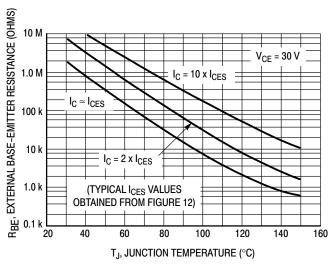
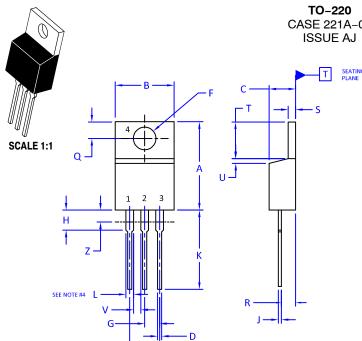


Figure 13. Effects of Base-Emitter Resistance

#### **ORDERING INFORMATION**

Device	Package	Shipping
TIP41G	TO-220 (Pb-Free)	50 Units / Rail
TIP41AG	TO-220 (Pb-Free)	50 Units / Rail
TIP41BG	TO-220 (Pb-Free)	50 Units / Rail
TIP41CG	TO-220 (Pb-Free)	50 Units / Rail
TIP42G	TO-220 (Pb-Free)	50 Units / Rail
TIP42AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42BG	TO-220 (Pb-Free)	50 Units / Rail
TIP42CG	TO-220 (Pb-Free)	50 Units / Rail

### **MECHANICAL CASE OUTLINE**



CASE 221A-09

**DATE 05 NOV 2019** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11	:	STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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